ABSTRACT

A semiconductor device is disclosed along with a manufacturing method thereof, which device includes a semiconductor element arranged to form integrated circuitry, a plurality of electrode pads as formed on the side of the integrated circuitry formation surface of the semiconductor element, bump electrodes for external connection as electrically connected to the electrode pads through a conductive layer, and a stress relaxation layer formed between the integrated circuitry formation surface and electrode pads on one hand and the bump electrodes and conductive layer on the other hand, the stress relax layer being adhered thereto, wherein more than one third of the stress relax layer from a surface thereof is cut away for removal and wherein the stress relax layer is subdivided into a plurality of regions. In accordance with the present invention, it is possible to provide a semiconductor device capable of offering high density mounting schemes with increased reliability while reducing production costs.